TOSHIBA

TOSHIBA DIODE SILICON EPITAXIAL PLANAR TYPE

155301

ULTRA HIGH SPEED SWITCHING APPLICATIONS.

• Small Package : SC-70

• Low Forward Voltage : V_{F(3)}=0.90V (Typ.)

• Fast Reverse Recovery Time : $t_{rr} = 1.6ns$ (Typ.)

• Small Total Capacitance : C_T=0.9pF (Typ.)

MAXIMUM RATINGS (Ta = 25°C)

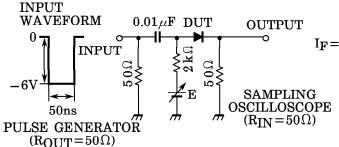
CHARACTERISTIC	SYMBOL	RATING	UNIT	
Maximum (Peak) Reverse Voltage	v_{RM}	85	V	
Reverse Voltage	$V_{\mathbf{R}}$	80	V	
Maximum (Peak) Forward Current	I_{FM}	300 (*)	mA	
Average Forward Current	IO	100 (*)	mA	
Surge Current (10ms)	I _{FSM}	2 (*)	A	
Power Dissipation	P	100	mW	
Junction Temperature	Tj	125	$^{\circ}\mathrm{C}$	
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~125	°C	

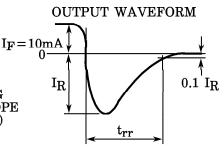
(*) Unit Rating. Total Rating=Unit Rating $\times 1.5$

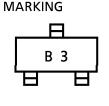
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

ELECTRICAL CHARACTERISTICS (Ta = 25°C)		weight . 0.000g					
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Forward Voltage	V _{F (1)}	I _F =1mA	_	0.60	_	V	
	$V_{F(2)}$	$I_{\mathbf{F}} = 10 \text{mA}$	_	0.72	_		
	$V_{F(3)}$	$I_{\mathbf{F}} = 100 \text{mA}$	_	0.90	1.20		
Reverse Current	$I_{R(1)}$	$V_R = 30V$	_		0.1	μ A	
	$I_{R(2)}$	$V_R = 80V$	_	_	0.5		
Total Capacitance	$\mathrm{c_{T}}$	$V_R=0$, f=1MHz	_	0.9	3.0	pF	
Reverse Recovery Time	$\mathfrak{t}_{\mathbf{rr}}$	$I_{ m F} = 10 { m mA, \ Fig.1}$	_	1.6	4.0	ns	

Fig.1 REVERSE RECOVERY TIME (t_{rr}) TEST CIRCUIT







961001EAA2

Unit in mm

 2.1 ± 0.1

 1.25 ± 0.1

ANODE1SS301-E(970507) ANODE

CATHODE

SC-70

1-2P1B

 1.3 ± 0.1

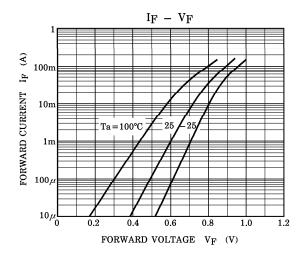
USM

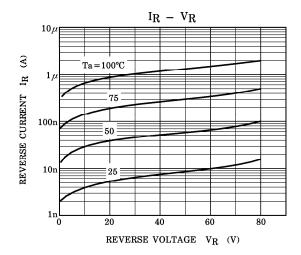
JEDEC EIAJ

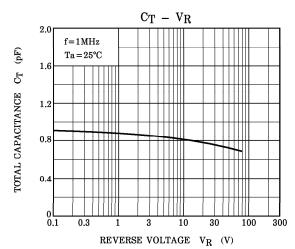
TOSHIBA

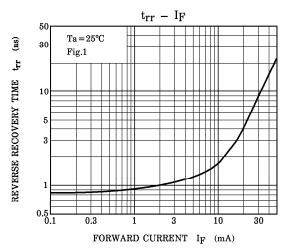
Weight · 0.006g

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